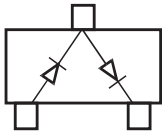


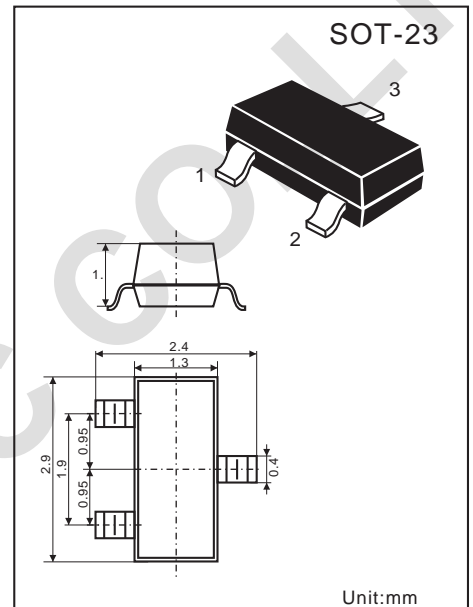
## SOT-23 Plastic-Encapsulate DIODE

## Features

- **Power dissipation**  
 $P_D$  : 150 mW ( $T_{amb}=25^{\circ}C$ )
- **Forward Current**  
 $I_F$  : 100 mA
- **Reverse Voltage**  
 $V_R$  : 80V
- **Operating and storage junction temperature range**  
 $T_j, T_{stg}$  :  $-55^{\circ}C$  to  $+150^{\circ}C$



Marking:C3



## ELECTRICAL CHARACTERISTICS

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse Voltage leakage current	$I_R$	$V_R=80V$		0.5	$\mu A$
Forward Voltage	$V_F$	$I_F=100mA$		1.2	V
Diode Capacitance	$C_{tot}$	$V_R=0V$ $f=1MHz$		3	pF
Reverse Recovery Time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		4	nS

Typical Characteristics

